

Polar™ Power MOSFET

HiPerFET™

IXFN44N100P

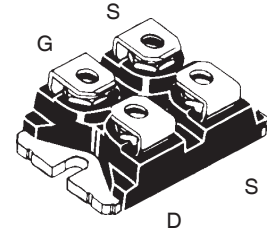
N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



$V_{DSS} = 1000V$
 $I_{D25} = 37A$
 $R_{DS(on)} \leq 220m\Omega$
 $t_{rr} \leq 300ns$

| Symbol | Test Conditions | Maximum Ratings | |
|---------------|--|-----------------|------------|
| | | | |
| V_{DSS} | $T_J = 25^\circ C$ to $150^\circ C$ | 1000 | V |
| V_{DGR} | $T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$ | 1000 | V |
| V_{GSS} | Continuous | ± 30 | V |
| V_{GSM} | Transient | ± 40 | V |
| I_{D25} | $T_C = 25^\circ C$ | 37 | A |
| I_{DM} | $T_C = 25^\circ C$, pulse width limited by T_{JM} | 110 | A |
| I_{AR} | $T_C = 25^\circ C$ | 22 | A |
| E_{AS} | $T_C = 25^\circ C$ | 2 | J |
| dV/dt | $I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$ | 20 | V/ns |
| P_D | $T_C = 25^\circ C$ | 890 | W |
| T_J | | -55 ... +150 | $^\circ C$ |
| T_{JM} | | 150 | $^\circ C$ |
| T_{stg} | | -55 ... +150 | $^\circ C$ |
| T_L | 1.6mm (0.062 in.) from case for 10s | 300 | $^\circ C$ |
| V_{ISOL} | 50/60 Hz, RMS | $t = 1min$ | 2500 V~ |
| | $I_{ISOL} \leq 1mA$ | $t = 1s$ | 3000 V~ |
| M_d | Mounting torque | 1.5/13 | Nm/lb.in. |
| | Terminal connection torque | 1.3/11.5 | Nm/lb.in. |
| Weight | | 30 | g |

miniBLOC, SOT-227 B (IXFN)
E153432



G = Gate
S = Source
D = Drain

Either Source terminal S can be used as the Source terminal or the Kelvin Source (gate return) terminal.

Features

- International standard package
- Encapsulating epoxy meets UL 94 V-0, flammability classification
- miniBLOC with Aluminium nitride isolation
- Fast recovery diode
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect

Advantages

- Easy to mount
- Space savings
- High power density

Applications

- Switched-mode and resonant-mode power supplies
- DC-DC Converters
- Laser Drivers
- AC and DC motor controls
- Robotics and servo controls

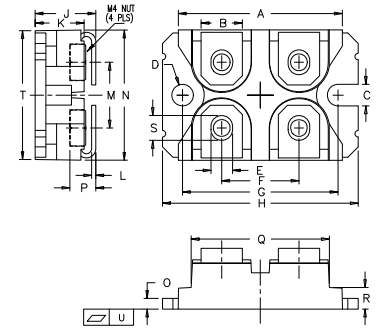
| Symbol | Test Conditions ($T_J = 25^\circ C$, unless otherwise specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|----------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 3mA$ | 1000 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 1mA$ | 3.5 | | 6.5 V |
| I_{GSS} | $V_{GS} = \pm 30V$, $V_{DS} = 0V$ | | | ± 200 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$ | | | 50 μA |
| | $V_{GS} = 0V$ | | | 3 mA |
| $R_{DS(on)}$ | $V_{GS} = 10V$, $I_D = 22A$, Note 1 | | | 220 m Ω |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|--------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $V_{DS} = 20\text{V}, I_D = 22\text{A}$, Note 1 | 20 | 35 | S |
| R_{Gi} | Gate input resistance | | 1.70 | Ω |
| C_{iss} | $V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$ | | 19 | nF |
| C_{oss} | | | 1060 | pF |
| C_{rss} | | | 41 | pF |
| $t_{d(on)}$ | Resistive Switching Times $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 22\text{A}$ $R_G = 1\Omega$ (External) | | 60 | ns |
| t_r | | | 68 | ns |
| $t_{d(off)}$ | | | 90 | ns |
| t_f | | | 54 | ns |
| $Q_{g(on)}$ | $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 22\text{A}$ | | 305 | nC |
| Q_{gs} | | | 104 | nC |
| Q_{gd} | | | 125 | nC |
| R_{thJC} | | | 0.14 | $^\circ\text{C/W}$ |
| R_{thCS} | | 0.05 | | $^\circ\text{C/W}$ |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified) | Characteristic Values | | |
|----------|---|-----------------------|------|---------------|
| | | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0\text{V}$ | | | 44 A |
| I_{SM} | Repetitive, pulse width limited by T_{JM} | | | 176 A |
| V_{SD} | $I_F = I_S, V_{GS} = 0\text{V}$, Note 1 | | | 1.5 V |
| t_{rr} | $I_F = 22\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$ | | | 300 ns |
| Q_{RM} | | | 2.5 | μC |
| I_{RM} | | | 17 | A |

Note 1: Pulse test, $t \leq 300\mu\text{s}$; duty cycle, $d \leq 2\%$.

SOT-227B Outline



| SYM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 1.240 | 1.255 | 31.50 | 31.88 |
| B | .307 | .323 | 7.80 | 8.20 |
| C | .161 | .169 | 4.09 | 4.29 |
| D | .161 | .169 | 4.09 | 4.29 |
| E | .161 | .169 | 4.09 | 4.29 |
| F | .587 | .595 | 14.91 | 15.11 |
| G | 1.186 | 1.193 | 30.12 | 30.30 |
| H | 1.496 | 1.505 | 38.00 | 38.23 |
| J | .460 | .481 | 11.68 | 12.22 |
| K | .351 | .378 | 8.92 | 9.60 |
| L | .030 | .033 | 0.76 | 0.84 |
| M | .496 | .506 | 12.60 | 12.85 |
| N | .990 | 1.001 | 25.15 | 25.42 |
| O | .078 | .084 | 1.98 | 2.13 |
| P | .195 | .235 | 4.95 | 5.97 |
| Q | 1.045 | 1.059 | 26.54 | 26.90 |
| R | .155 | .174 | 3.94 | 4.42 |
| S | .186 | .191 | 4.72 | 4.85 |
| T | .968 | .987 | 24.59 | 25.07 |
| U | -.002 | .004 | -0.05 | 0.1 |

IXYS reserves the right to change limits, test conditions, and dimensions.

| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| | 4,850,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

Fig. 1. Output Characteristics @ 25°C

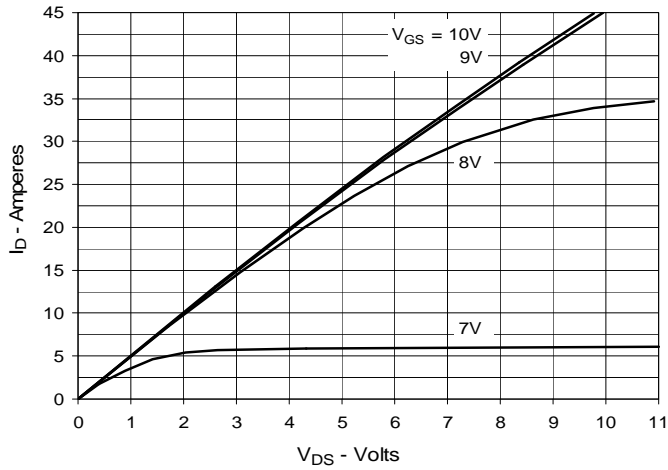


Fig. 2. Extended Output Characteristics @ 25°C

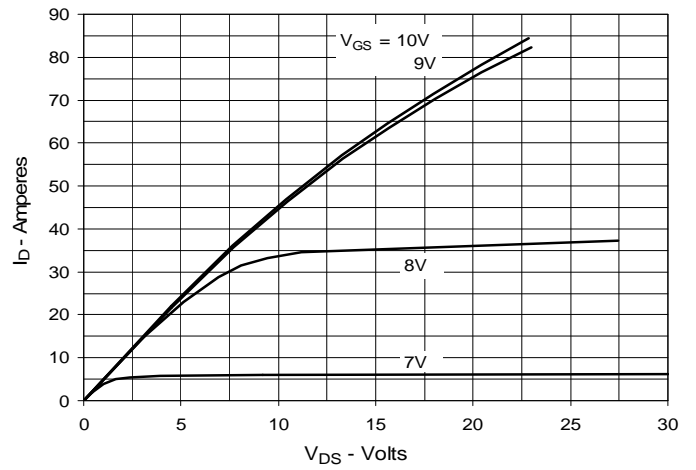


Fig. 3. Output Characteristics @ 125°C

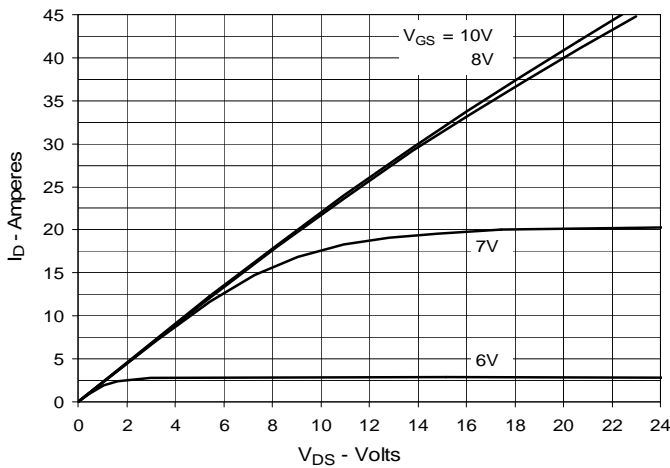


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 22A$ Value vs. Junction Temperature

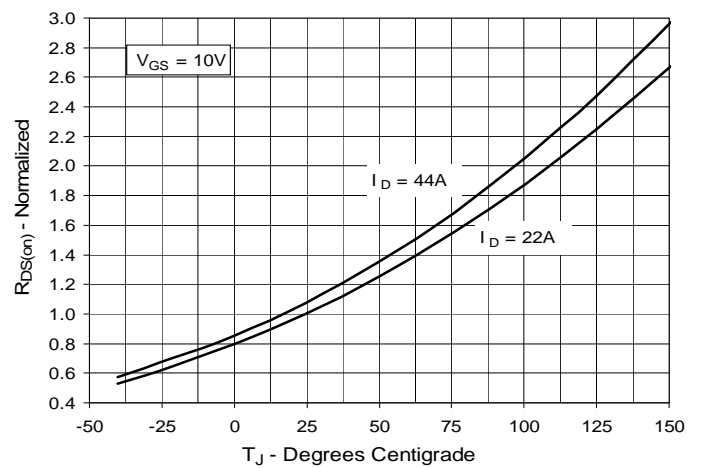


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 22A$ Value vs. Drain Current

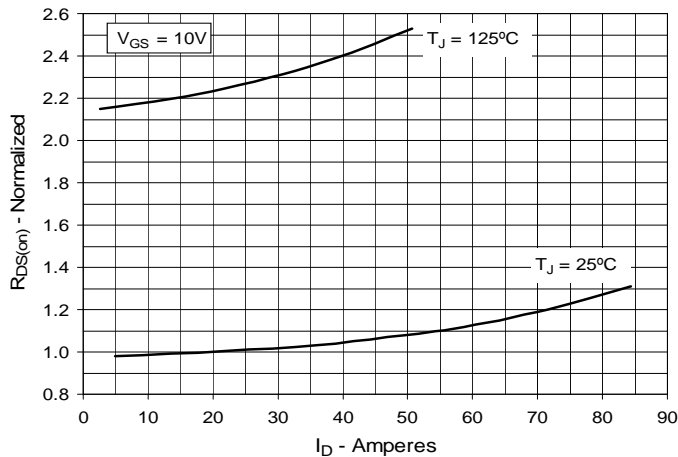


Fig. 6. Maximum Drain Current vs. Case Temperature

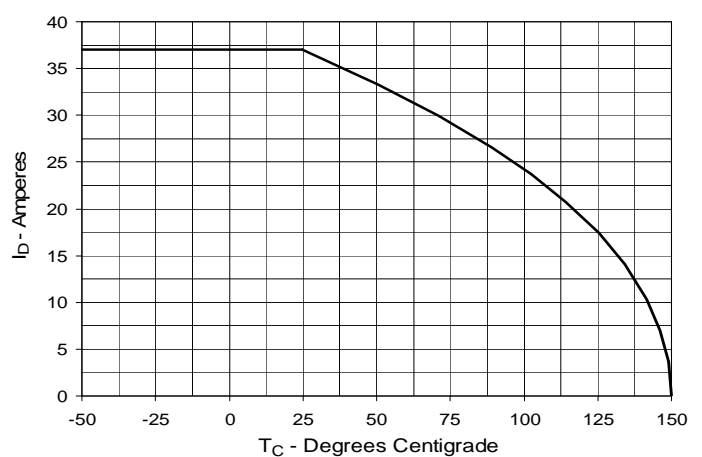
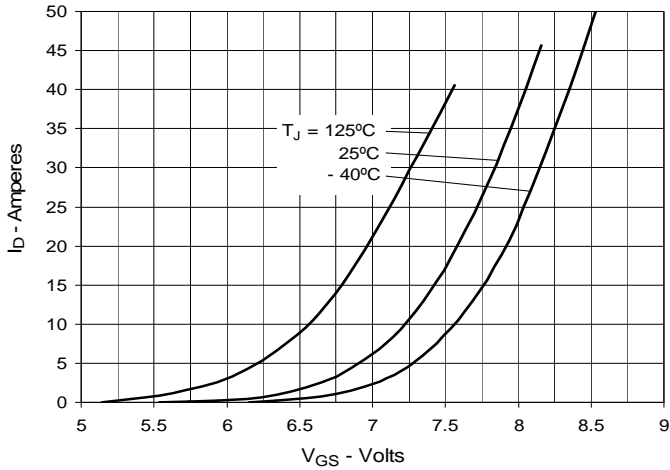
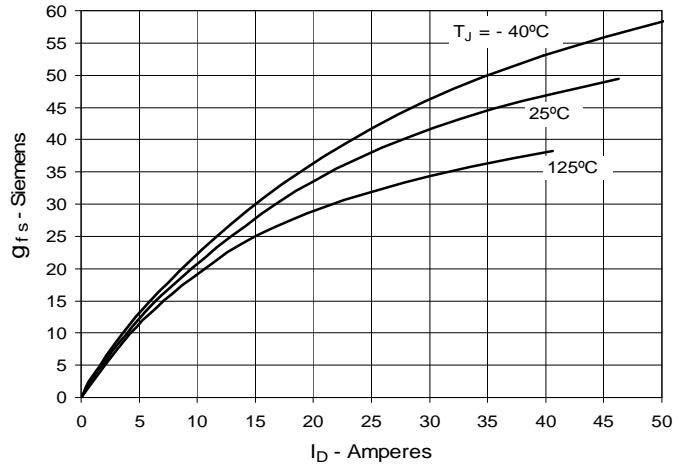
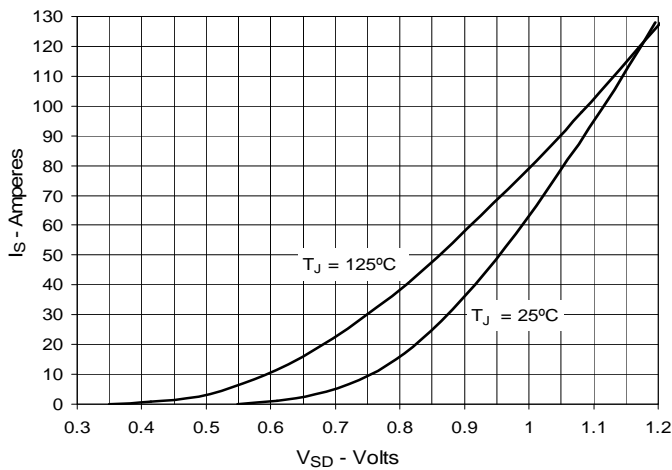
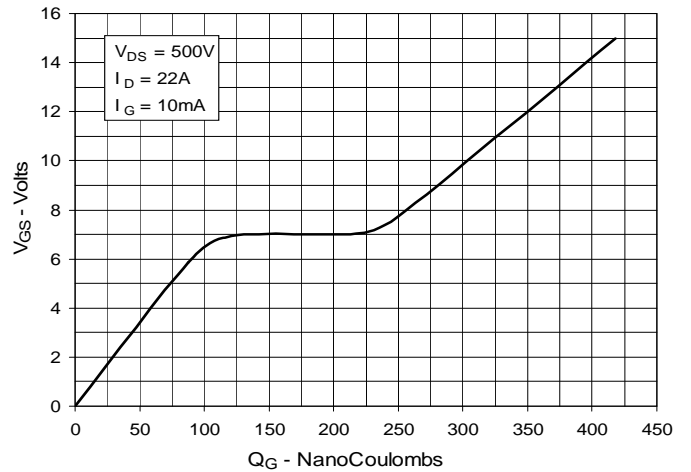
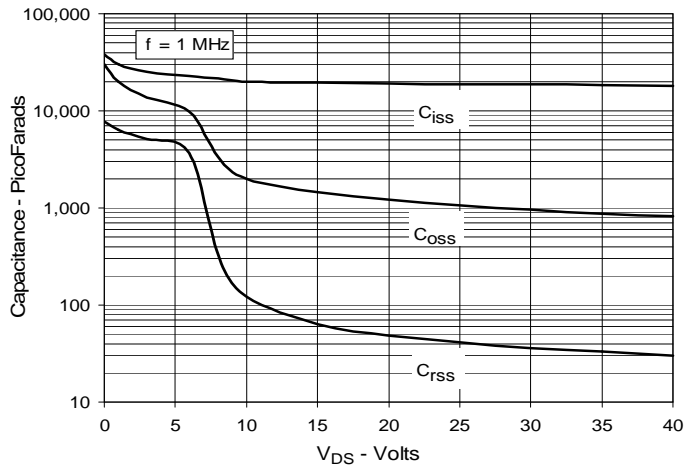


Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Forward Voltage Drop of Intrinsic Diode

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Maximum Transient Thermal Impedance
